MUR180E, MUR1100E

MUR1100E is a Preferred Device

SWITCHMODE™ Power Rectifiers

Ultrafast "E" Series with High Reverse Energy Capability

These state−of−the−art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- 10 mjoules Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 V
- These are Pb−Free Devices*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in Plastic Bags; 1,000 per Bag
- Available Tape and Reel; 5,000 per Reel, by Adding a "RL" Suffix to the Part Number
- Polarity: Cathode Indicated by Polarity Band

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MUR180E MUR1100E	V_{RRM} V_{RWM} V_R	 800 1000	V
Average Rectified Forward Current (Note 1) (Square Wave Mounting Method #3 Per Note 3)	$I_{F(AV)}$	1.0 @ T_A = 95°C	A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	35	A
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	−65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

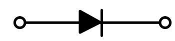
1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

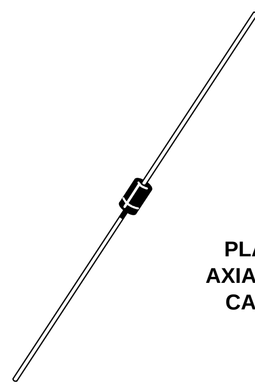
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

http://onsemi.com

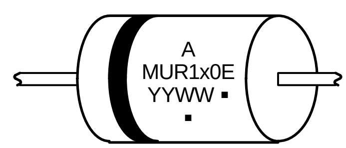
ULTRAFAST RECTIFIERS
1.0 AMPERES, 800−1000 VOLTS





PLASTIC
AXIAL LEAD
CASE 59

MARKING DIAGRAM



A = Assembly Location
MUR1x0E = Device Code
x 8 or 10
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

July, 2006 − Rev. 3

Publication Order Number:
MUR180E/D

THERMAL CHARACTERISTICS

Charateristics	Symbol	Value	Unit
Maximum Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	See Note 3	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2) (i_F = 1.0 Amp, T_J = 150°C) (i_F = 1.0 Amp, T_J = 25°C)	v_F	 1.50 1.75	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_J = 100°C) (Rated dc Voltage, T_J = 25°C)	i_R	 600 10	μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 Amp)	t_{rr}	 100 75	ns
Maximum Forward Recovery Time (I_F = 1.0 Amp, di/dt = 100 Amp/μs, Recovery to 1.0 V)	t_{fr}	75	ns
Controlled Avalanche Energy (See Test Circuit in Figure 6)	W_{AVAL}	10	mJ

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping†
MUR180E	Axial Lead*	1000 Units / Bag
MUR180EG	Axial Lead*	
MUR180ERL	Axial Lead*	5000 / Tape & Reel
MUR180ERLG	Axial Lead*	
MUR1100E	Axial Lead*	1000 Units / Bag
MUR1100EG	Axial Lead*	
MUR1100ERL	Axial Lead*	5000 / Tape & Reel
MUR1100ERLG	Axial Lead*	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*These packages are inherently Pb−Free.

ELECTRICAL CHARACTERISTICS

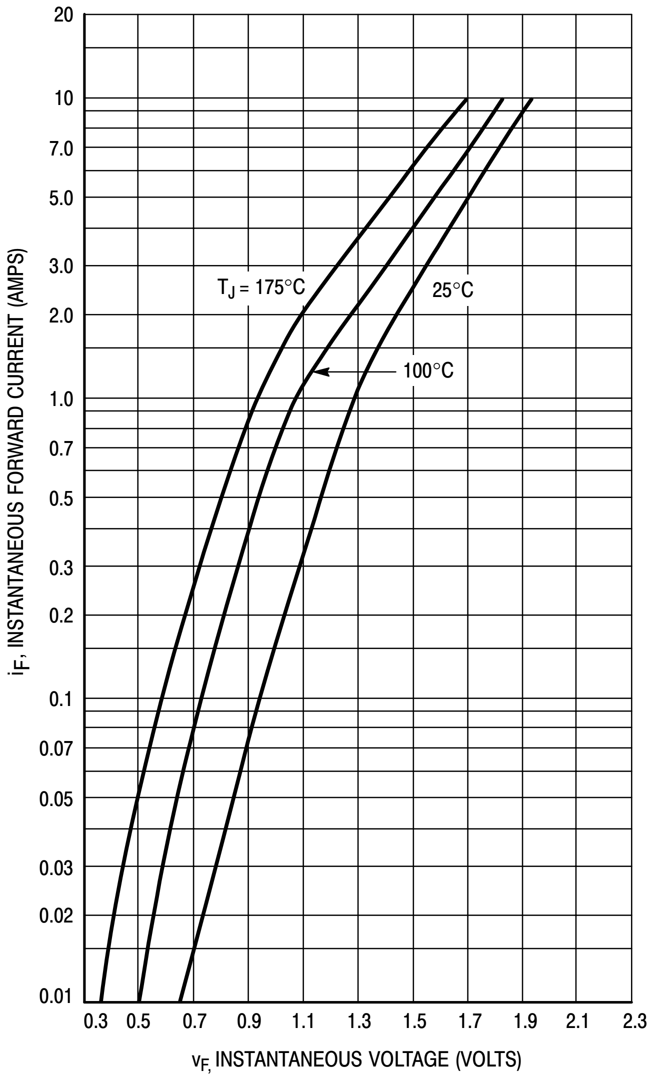


Figure 1. Typical Forward Voltage

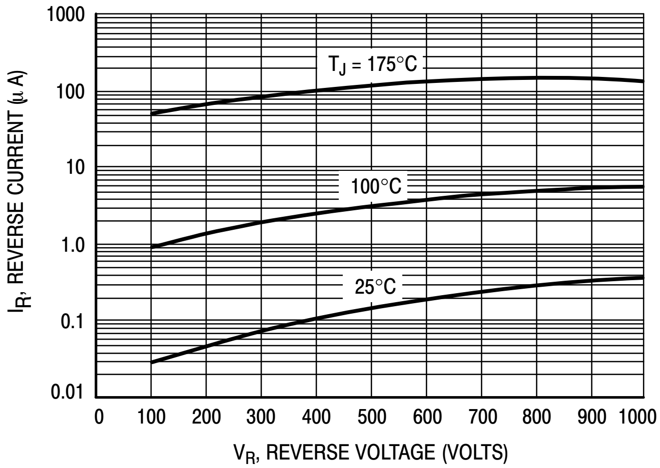


Figure 2. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

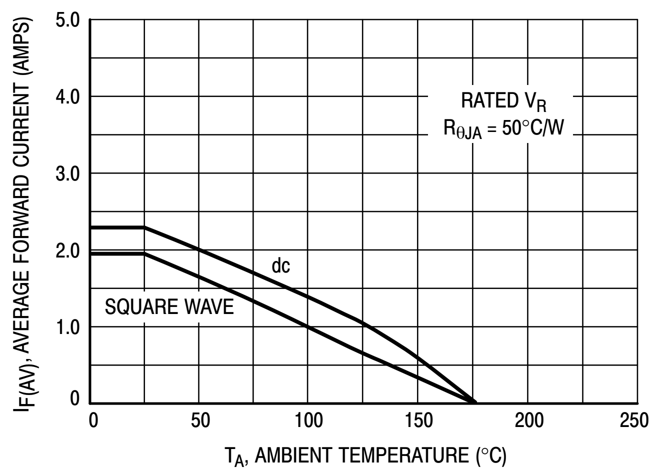


Figure 3. Current Derating (Mounting Method #3 Per Note 3)

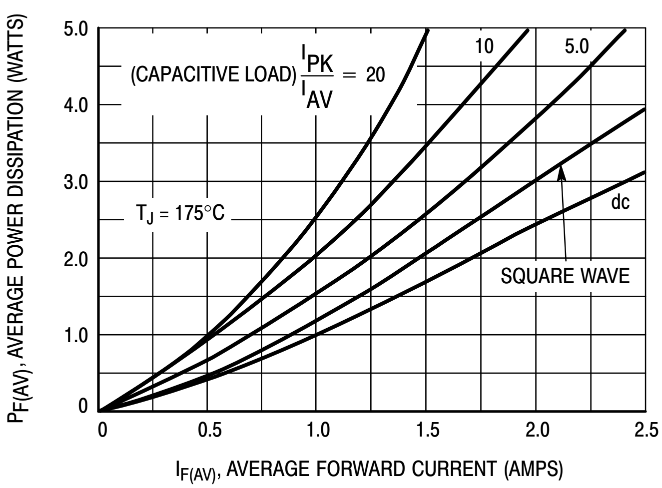


Figure 4. Power Dissipation

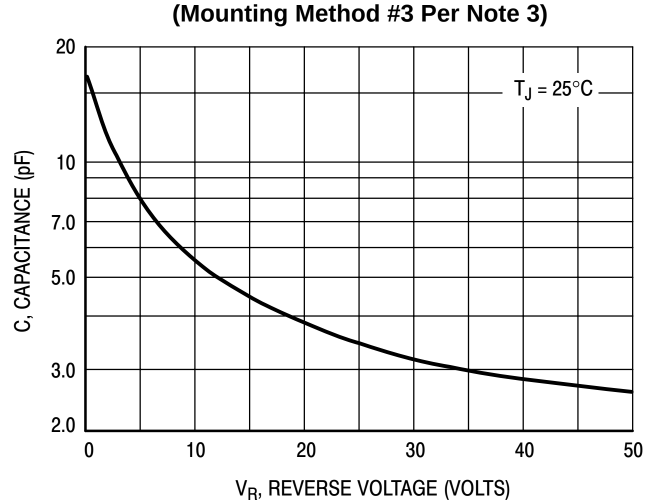


Figure 5. Typical Capacitance

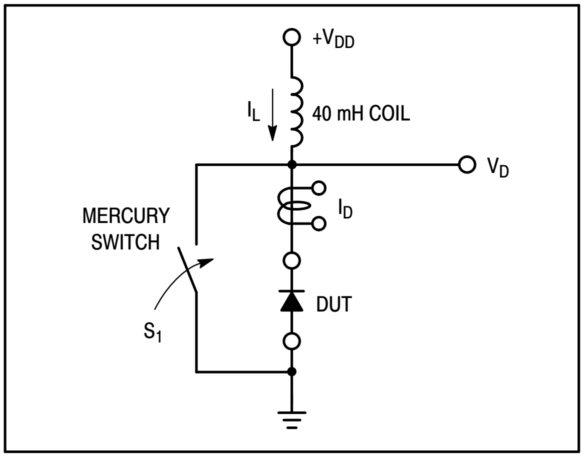


Figure 6. Test Circuit

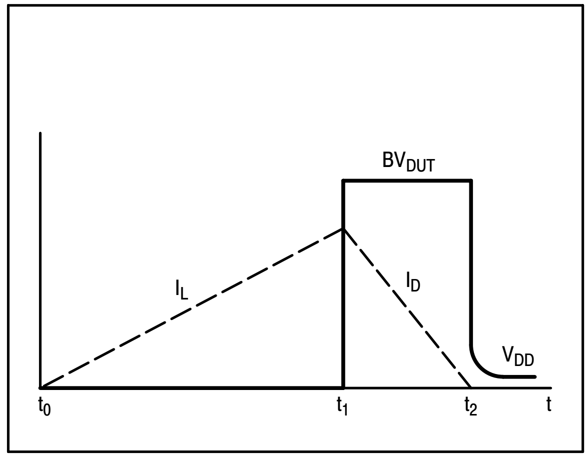


Figure 7. Current−Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 6 was used to demonstrate the controlled avalanche capability of the new "E'' series Ultrafast rectifiers. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2.

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

The oscilloscope picture in Figure 8, shows the information obtained for the MUR8100E (similar die construction as the MUR1100E Series) in this test circuit conducting a peak current of one ampere at a breakdown voltage of 1300 V, and using Equation (2) the energy absorbed by the MUR8100E is approximately 20 mjoules.

Although it is not recommended to design for this condition, the new "E'' series provides added protection against those unforeseen transient viruses that can produce unexplained random failures in unfriendly environments.

EQUATION (1):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2 \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2$$

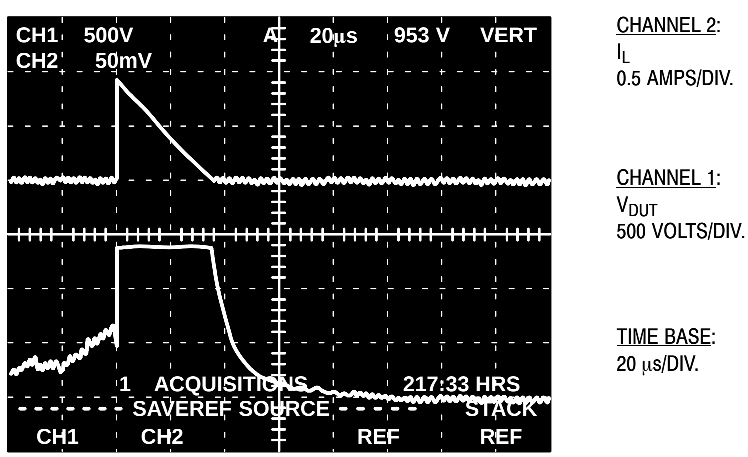


Figure 8. Current−Voltage Waveforms

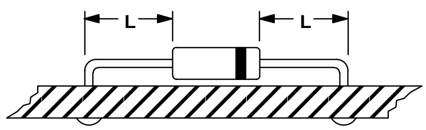
NOTE 3 — AMBIENT MOUNTING DATA

Data shown for thermal resistance, junction−to−ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

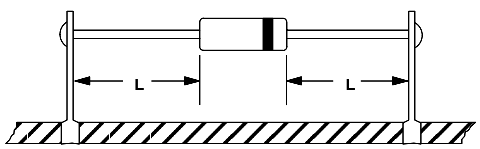
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting Method		Lead Length, L			Units
		1/8	1/4	1/2	
1	$R_{\theta JA}$	52	65	72	°C/W
2	$R_{\theta JA}$	67	80	87	°C/W
3	$R_{\theta JA}$	50			°C/W

MOUNTING METHOD 1

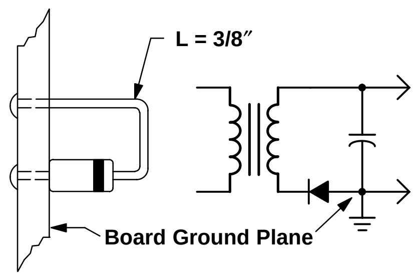


MOUNTING METHOD 2



Vector Pin Mounting

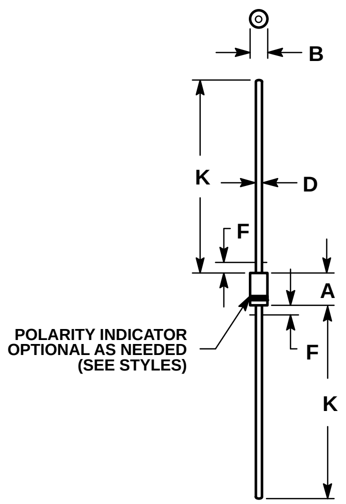
MOUNTING METHOD 3



P.C. Board with
1−1/2″ X 1−1/2″ Copper Surface

PACKAGE DIMENSIONS

AXIAL LEAD
CASE 59−10
ISSUE U



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO−41 OUTLINE SHALL APPLY
4. POLARITY DENOTED BY CATHODE BAND.
5. LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.161	0.205	4.10	5.20
B	0.079	0.106	2.00	2.70
D	0.028	0.034	0.71	0.86
F	−−−	0.050	−−−	1.27
K	1.000	−−−	25.40	−−−

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

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PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative